

1. PRODUCT Schottky barrier Diode (Silicon Epitaxial Planar)
2. TYPE RB150M-30
3. APPLICATION General rectification
4. FEATURE Small power mold type (PMDU)
High reliability
Low VF

5. ABSOLUTE MAXIMUM RATING (Ta=25°C)

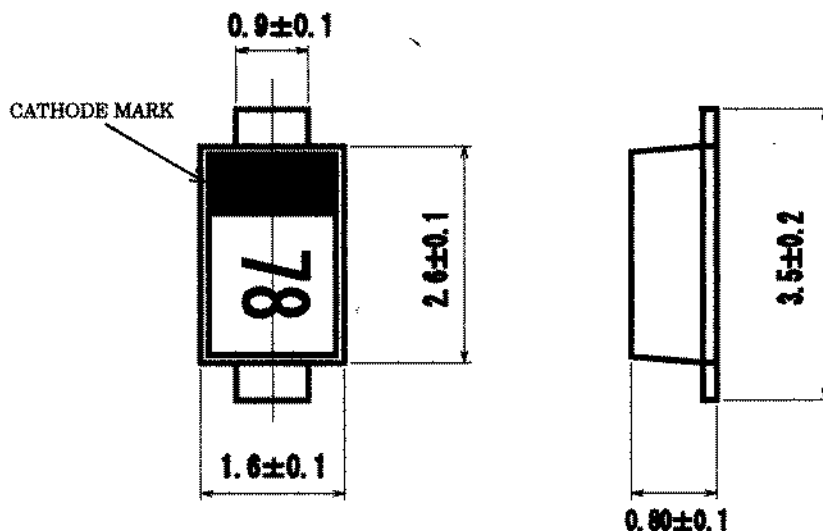
Reverse voltage(repetitive peak)	VRM		30 V
Reverse voltage(DC)	VR		30 V
Average rectified forward current	(*) Io		1.5 A
Forward current surge peak (60Hz·1cyc.)	IFSM		30 A
Junction temperature	Tj		150 °C
Storage temperature	Tstg		-40~150 °C
[(*)Glass epoxy substrate at the time of assembler, half sine wave at 180°C Tc=90°C max]			

6. ELECTRICAL CHARACTERISTIC (Ta=25°C)

Characteristic	Symbol	Test condition	Standard	
			TYP.	MAX.
Forward voltage	VF1	IF= 0.5 A	0.39 V	0.46 V
	VF2	IF= 1.0 A	0.43 V	0.48 V
Reverse current	IR1	VR= 15 V	3.0 μA	20 μA
	IR2	VR= 30 V	9.0 μA	50 μA
Thermal resistance	Rth(j-a)	at mounted on epoxy board land pattern : 6*6mm	142.8 °C/W	-

* Please pay attention to static electricity when handling.

7. DIMENSION (UNIT:mm)



8. Mass per piece 10 mg/pcs

DESIGN	CHECK	APPROVAL	DATE:AUG.08.2002	SPECIFICATION No. : RB150M-30*ENG
			REV.A	ROHM CO., LTD.